

TYPE AND VOLTAGE

W-TYPE:	UL and CSA type	120V AC
E -TYPE:	NK-STD type	220V AC
B -TYPE:	BS type	240V AC

SERVICE MANUAL

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SPECIFICATIONS

AMPLIFIER SECTION

Continuous Power Output per Channel:

- 20 ~ 20000 Hz (8 ohms) more than 120 Watts
- 20 ~ 20000 Hz (4 ohms) more than 130 Watts
- 1000 Hz (8 ohms) more than 120 Watts
- 1000 Hz (4 ohms) more than 130 Watts

T. H. Distortion, 8 ohms:

- at Continuous Power Output . . . no more than 0.008%
- at 1 Watt Power Output no more than 0.02%

T. H. Distortion, 4 ohms:

- at Continuous Power Output . . . no more than 0.02%

I. M. Distortion, 8 ohms:

- at Continuous Power Output . . . no more than 0.01%
- at 1 Watt Power Output no more than 0.02%

IHF Power Bandwidth, 8 ohms: 5 ~ 70000Hz

Damping Factor at 1000 Hz, 8 ohms: more than 60

Frequency Response, "NORMAL" input, 8 ohms:

at 1 Watt power Output . . . 10 ~ 100000Hz +0, -1dB

Input Sensitivity for 120 Watts Power Output:

MAIN IN 1V ± 2dB

Signal to Noise Ratio, IHF "A" Network:

MAIN (NORMAL, DIRECT) better than 105dB

Signal to Noise Ratio, DIN Filter:

MAIN IN (NORMAL, DIRECT) . . . better than 90dB

Channel Balance: no more than 1dB

Residual Hum and Noise, 8 ohms: . . . no more than 0.5mV

Idling Current: 40 ~ 120mA

Midpoint Voltage: 0 ± 20mV

Muting Delay Time: 3 ~ 7 seconds

GENERAL

Power Requirement:

- W-TYPE AC 120V, 60Hz
- E-TYPE AC 220V, 50Hz
- B-TYPE AC 240V, 50Hz

Power Consumption: 480 W (620 VA)

Ambient Temperature during Operation: . . . -10 ~ 30°C

Dimensions:

- Width 482 mm (19 inches)
- Height 138 mm (5 1/3 inches)
- Depth 344 mm (13 1/2 inches)

Weight, without package: 13.5 kg (29.7 lbs)

*Specifications are subject to change without notice.

BLOCK DIAGRAM

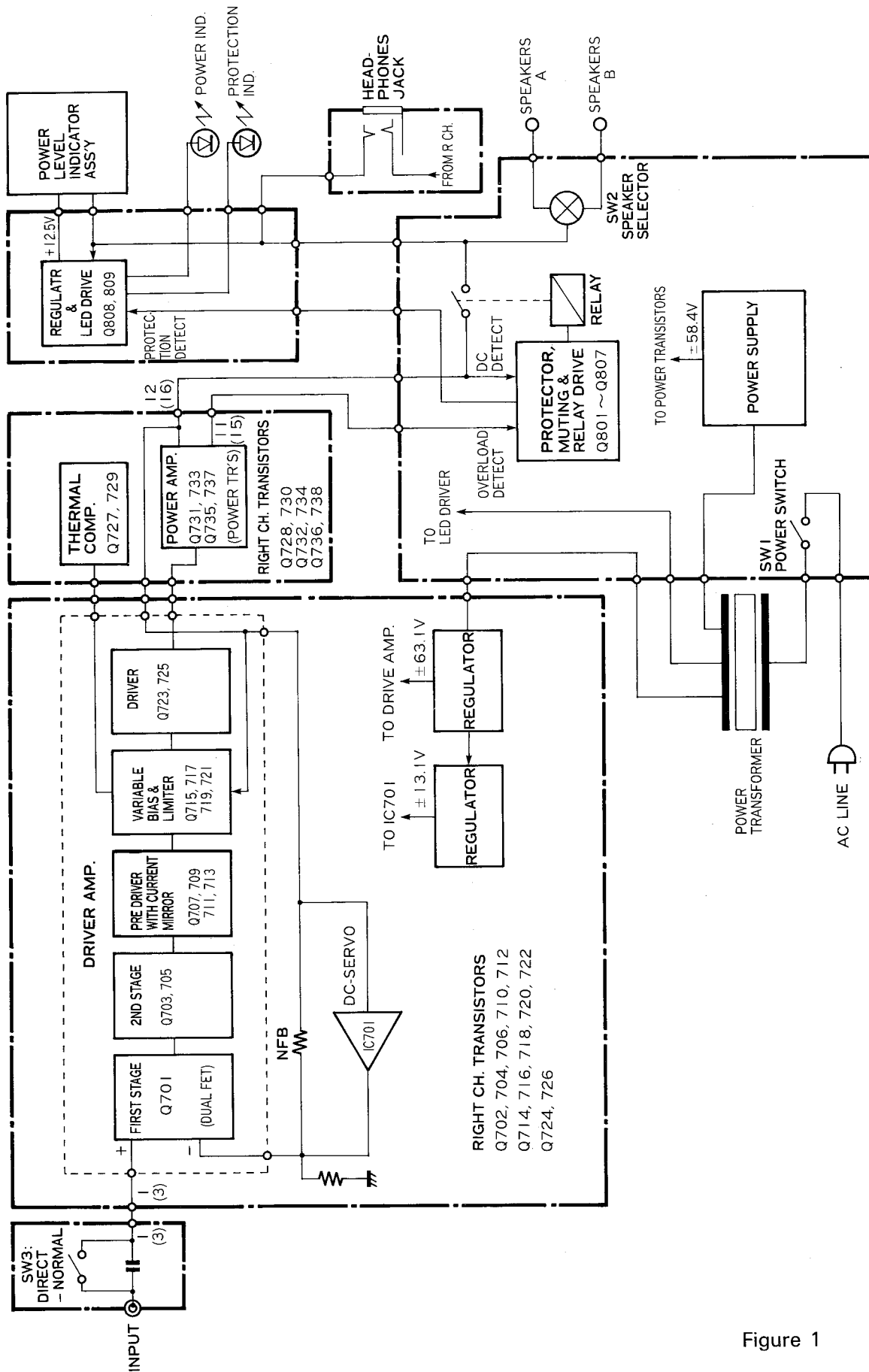


Figure 1

DISASSEMBLY

CABINET COVER REMOVAL

- Remove four tapping screws from the top of the unit.
- Remove four screws from both sides of the unit.
- Lift the cabinet cover away from the unit.

BOTTOM PLATE REMOVAL

- Remove nine tapping screws from the bottom of the unit as shown in Photo 1. (#1 – #9)
- Lift the bottom plate away from the unit.

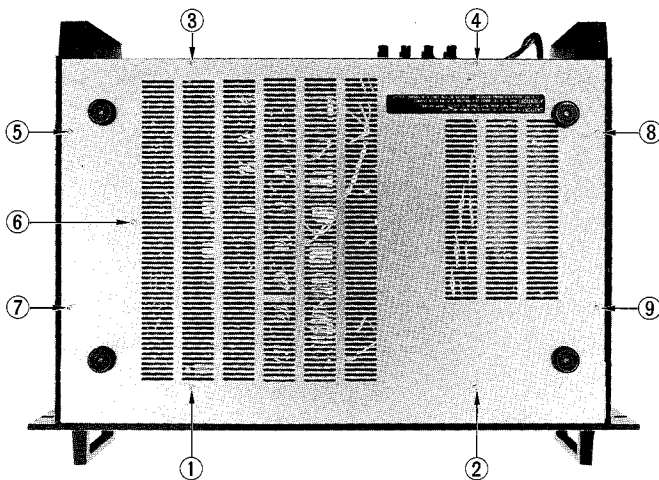


Photo 1

FRONT PANEL REMOVAL

- Remove three tapping screws (#1 – #3) from the left side of the unit as shown in Photo 2.
- Similarly remove three tapping screws from the right side of the unit.
- Remove the front panel away from the unit by pulling it forward.

POWER TRANSFORMER REMOVAL

- Remove the cabinet cover and the bottom plate.
- Disconnect all the cables from the power transformer.
- Remove four nuts (#1 – #4) from the chassis as shown in Photo 3.
- Lift the power transformer away from the unit.

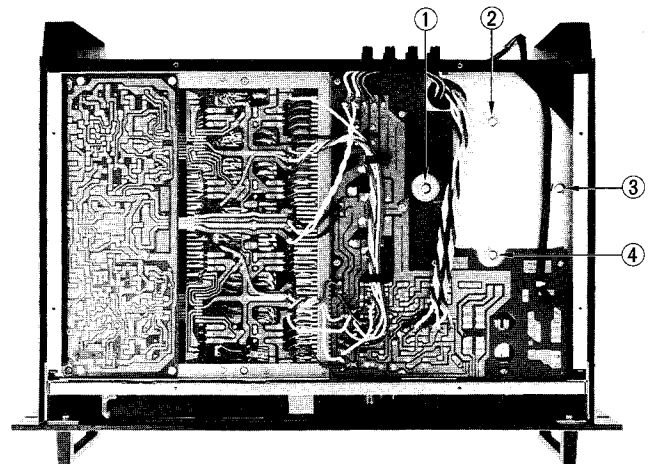


Photo 3

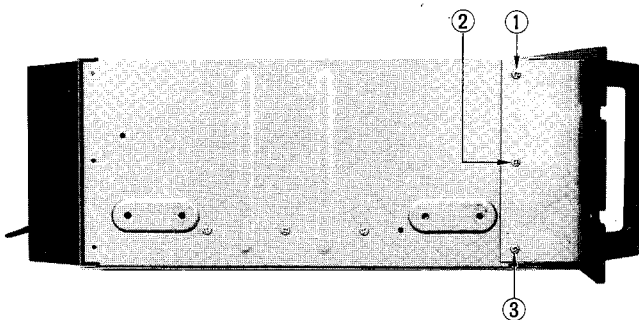


Photo 2

CIRCUIT DESCRIPTION

NIKKO's ALPHA 220, adopting latest devices such as Hi-FT power transistors, is of a design introducing a variable bias circuit (non-switching circuit), a DC servo circuit and other most advanced techniques.

For details, refer to page 2 "BLOCK DIAGRAM" and page 8 "SCHEMATIC DIAGRAM".

The following are explanations of the main circuits and devices.

1. VARIABLE BIAS CIRCUIT

Currently, in the output stage of power amplifiers are mostly used SEPP (Single Ended Push Pull) circuits. (Fig. 2).

It is generally known that the current (idle current) flowing through NPN and PNP transistors of this circuit can be classified into three large groups of operation form, class "A", class "AB" and class "B". (Fig. 3).

In class "A" operation, neither of collector currents, Q_1 and Q_2 , becomes zero nor cut off. Even when the current flowing to the load R_L is zero, a certain current is flowing through Q_1 and Q_2 , and so no crossover distortion exists theoretically.

To realize perfect class "A" operation, however, a current equal to or more than maximum output should continue to be let flow at the output stage as idle current, causing class "A" operation to prove to

be a poor efficiency system.

In class "AB" or "B" operation, the Q_1 plays the role of amplification of the plus part of the signal and Q_2 that of the minus part, no matter whether idle current is large or small.

In other words, there definitely exists a period in which, when one transistor is on, the other transistor keeps cutting off, in these operations.

Switching distortion or crossover distortion is caused at the moment of this active status turning into cut-off status or the cut-off status into the active status. Nevertheless, as these operation forms have high efficiency with small idle current, it is much easier to use class "AB" or "B" operation for high power amplification rather than class "A".

A power amplifier enjoying the merit of each of these systems — that is, practically no crossover or switching distortion being caused in class "A" operation and easier high power amplification being achieved by class "B" — has been realized by adopting the variable bias circuit.

The idea of a variable bias circuit is that in no case the output stage is allowed to be cut-off by increasing and decreasing bias voltage in corresponding with the voltage of input signal.

Fig. 4 shows the variable bias circuit adopted in ALPHA 220.

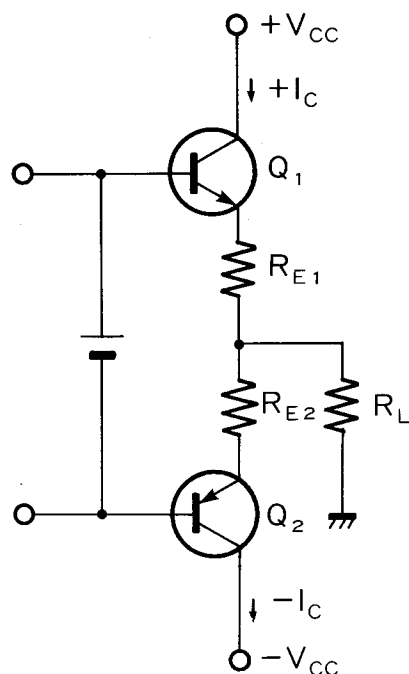


Figure 2 SEPP CIRCUIT

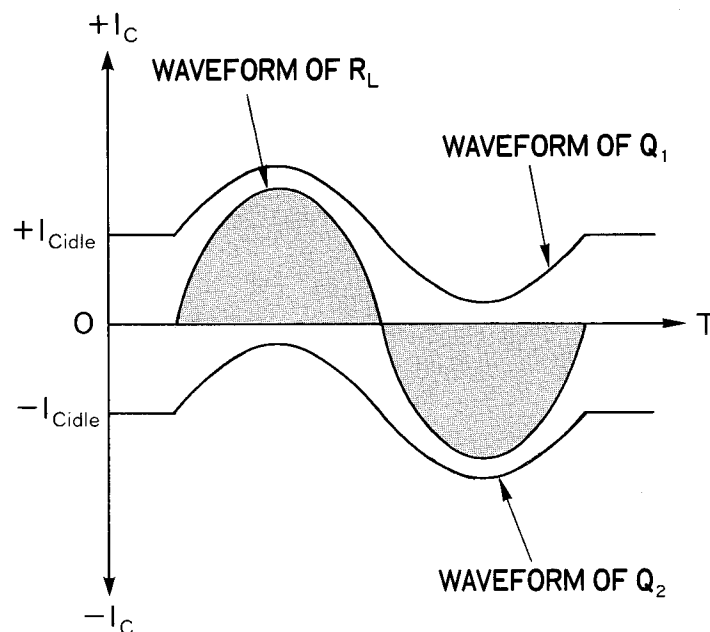


Figure 3-1 CLASS-A OPERATION

Now, suppose the plus wave (plus part) of signal has been inputted, the current of Q_{p1} increases and the voltage at both ends of RE_1 become high, resulting in the voltage between (A) point and OUTPUT. At that time, the voltage at both ends of R_1 becomes high because current flows $R_1 \rightarrow D_1 \rightarrow Q_1$, causing the potential at (C) point to lower and the voltage of Q_3 between collector and emitter to rise.

As a result, the voltage between (A) and (B) rises and Q_{p2} is kept from being cut-off.

From another point of view, the voltage drops at the emitter resistor RE_1 (these resistors are indispensable to protect transistors in stabilizing bias of the output stage or at the time of abnormal current flowing) is cancelled by the drop at R_1 , thus protecting Q_{p2} from becoming zero or anti-bias.

In the same manner, when the minus wave (minus part) of signal has been inputted, current flows $Q_2 \rightarrow D_2 \rightarrow R_2$, resulting in a rise of V_{CE} at Q_4 thus protecting Q_{p1} from being cut-off.

2. DC SERVO CIRCUIT

DC amplification is the most advanced form adopted for audio amplifiers as there is no phase lag over all the range from DC to audio frequency.

However, in a perfect DC amplifier (which is an amplifier having no coupling capacitors in its input part and NFB loop), a DC drift is caused in case a direct current is inputted or when the DC balance between each element has been lost due to temperature rise

inside the amplifier. The DC servo circuit is to suppress such a drift and realize a more stabilized amplifier.

The principle of a DC servo circuit is something like that of a comparator, in which changes in DC current between the output point and the ground is detected and drifts of the amplifier is controlled with their results used as the output of the servo circuit.

The basic elements are an integrating circuit composed of C_1 and R_1 , an operational amplifier and a mirror integrator composed of C_2 and R_2 . (Fig. 5).

Now, suppose a drift Δe_o has been caused at the output of the power amplifier, a potential with the same phase Δe_f is outputted at the output of the operational amplifier.

On the other hand, the initial stage of the power amplifier is a differential amplifier. When Δe_f is inputted at its inverting input, the potential at the non-inverting input Δe_i changes in the opposite direction of Δe_f , resulting in a decrease of drift at the output of the power amplifier.

The DC servo circuit has a specific frequency characteristic. In the range of DC and ultra low frequency, gain of the power amplifier is kept at one over several tens of decibel, and in the audio frequency band, amplification at a certain gain can be made in the same manner as ordinary power amplifier.

The frequency on which the DC servo circuit starts to have effects is determined by the four elements, C_1 , R_1 , C_2 and R_2 .

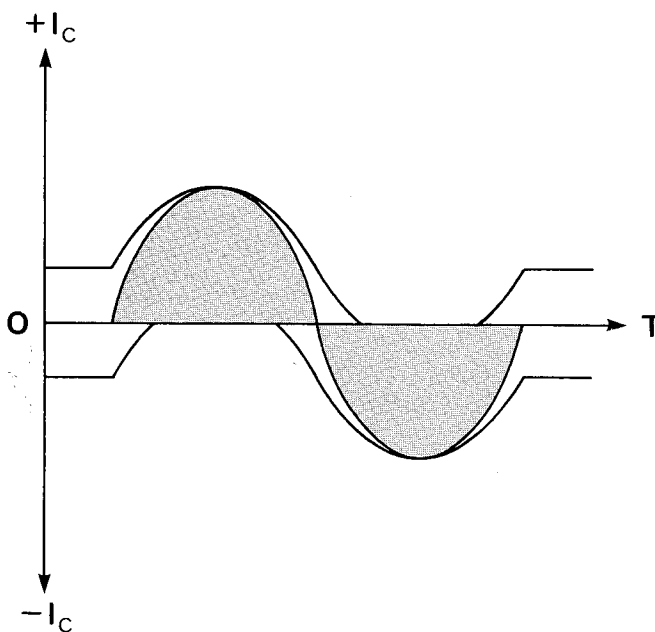


Figure 3-2 CLASS-AB OPERATION

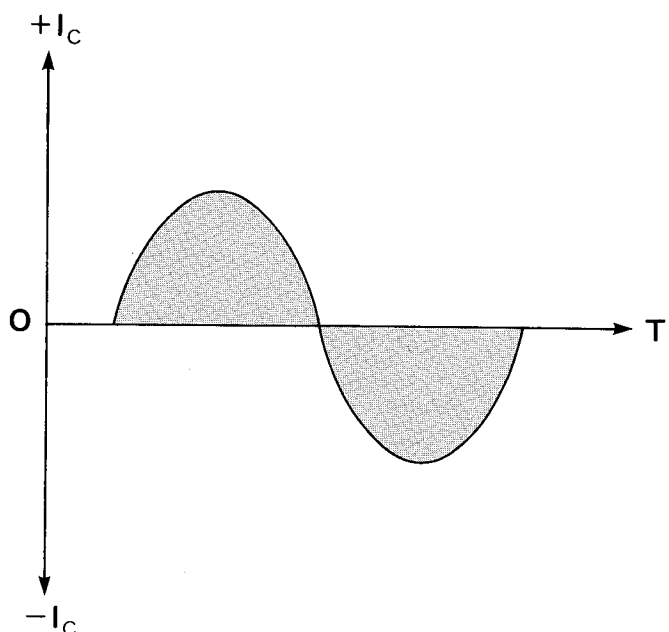


Figure 3-3 CLASS-B OPERATION

PARTS LOCATION

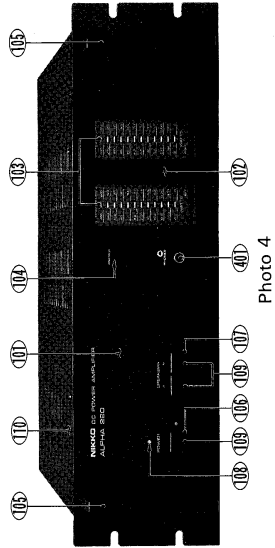


Photo 4

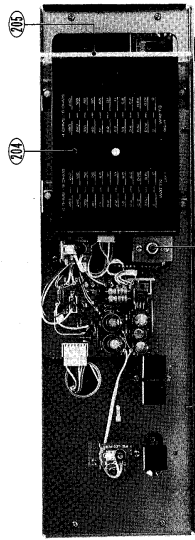


Photo 5

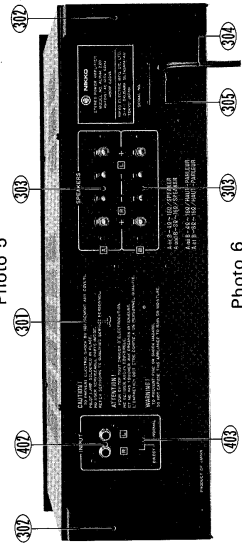


Photo 6

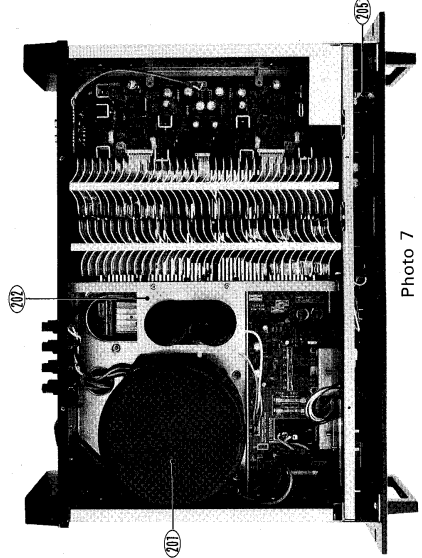


Photo 7

3. HI-FT POWER TRANSISTORS

For details characteristics, refer to "SEMICONDUCTOR DATA" at the end of this manual.

The power transistors employed in ALPHA 220 realize an FT (Current Gain-bandwidth Product) of 80 MHz with NPN type and 60 MHz with PNP type (each being a typical value) in spite of its high P_c (Collector Power Dissipation) such as 150 W (The value when T_c = 25° C). Compared with conventional transistors with a P_c of 150 W where FT was around 10 MHz at maximum, the high speed attained by these Hi-FT power transistors is remarkable.

Such high FT has been realized specially by the inside construction of these transistors which is greatly different from that of conventional ones — the multi-emitter construction.

In this construction, the emitter inside the transistor is divided into many units and emitter resistors with small resistance are inserted to each unit, resulting in a parallel connection.

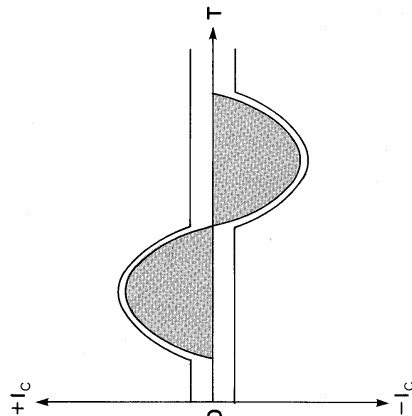


Figure 3-4 OPERATION OF BARIAYLE BIAS

This equivalently means that many small signal transistors with high FT and switching speed are parallelly connected, which has made it possible to realize such a high power characteristic while maintaining high switching speed.

Thanks to such construction as mentioned above, these power transistors are excellent in linearity of its *h*_{fe}.

Furthermore, as dissipation is dispersed equally to each emitter due to the emitter-divided construction, they have another feature of being strong against breakdown as compared with conventional power transistors.

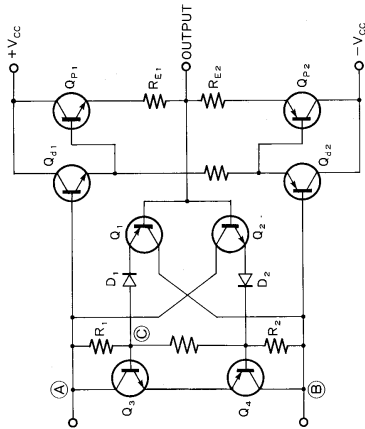


Figure 4 VARIABLE-BIAS CIRCUIT

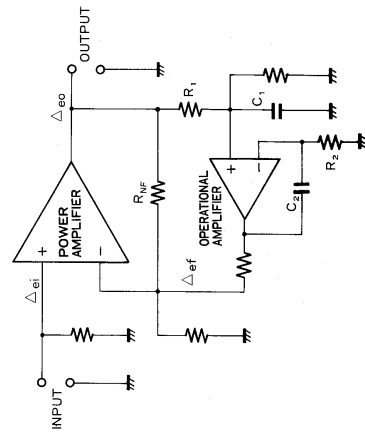
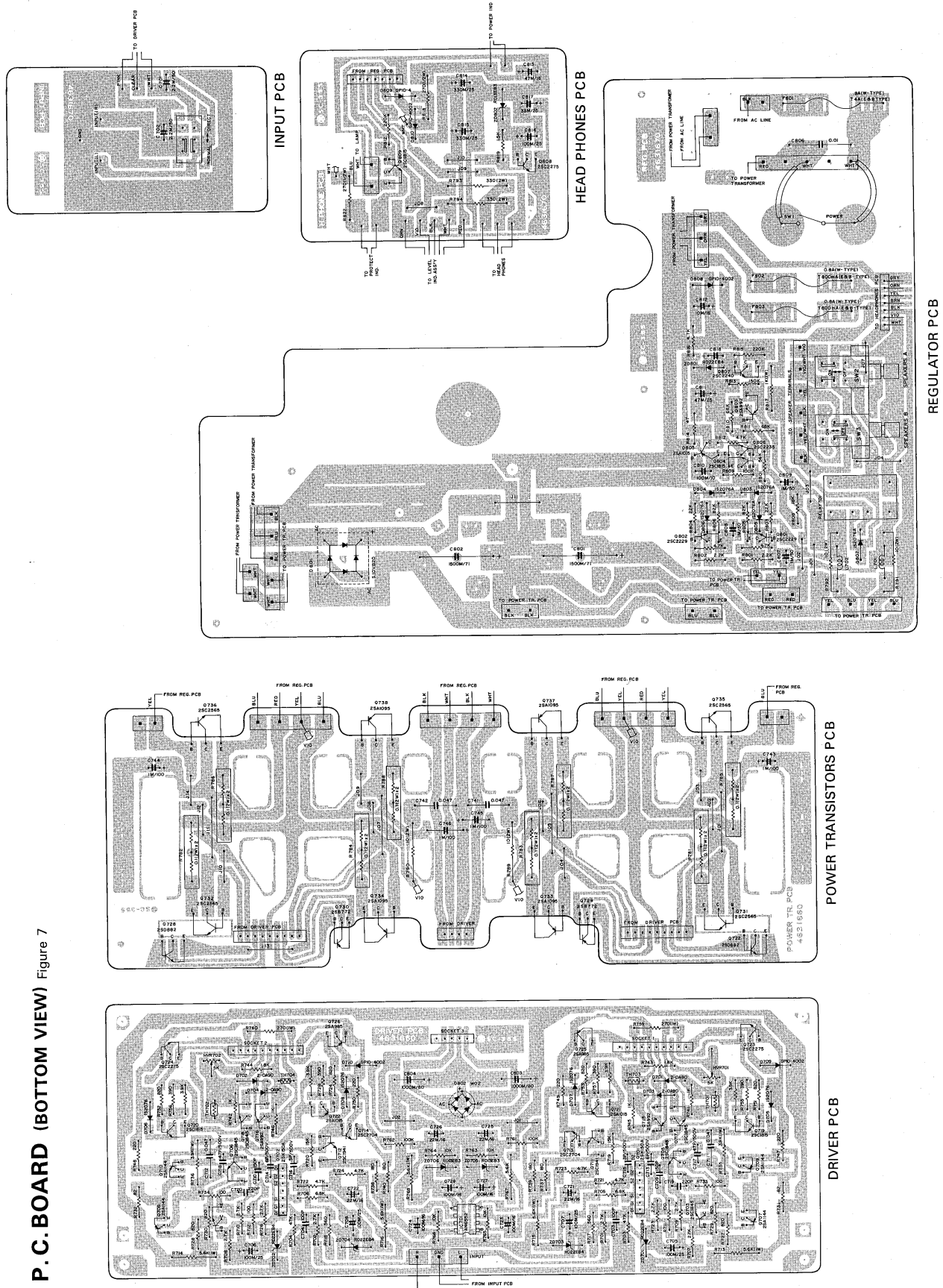


Figure 5 DC-SERVO CIRCUIT

P. C. BOARD (BOTTOM VIEW) Figure 7



ALIGNMENT

ALIGNMENT PRECAUTIONS

1. As the ALPHA 220 is a power amplifier with large output power, it consumes much electrical power and a great amount of current flows in the power source line of the primary side. Therefore, in the case when it is connected to the source by an extension cord, the size of the extension cord should be equal or larger than that of the power source cord of the ALPHA 220. Otherwise, the voltage might be reduced or the extension cord might generate excessive heat because of the resistance which the cord has, then not only can proper alignment be done, but also it is very dangerous.
2. If the power sources are supplied to the ALPHA 220 and the instruments by branching off from one cord, the voltage is sometimes dropped down and the stability of the instruments goes down.
The ALPHA 220 and the instruments should be connected to the power sources by using independent cords. The ALPHA 220 must take the power source from AC outlet of the wall side.
3. As there are many parts which hold high voltages in the circuit and the parts inside of the ALPHA 220, be careful not to receive an electric shock. In the case of connecting and taking off the instruments, you must turn off the power switch of the ALPHA 220 before getting on the work.
4. When the circuit happens to be shorted by the drivers or test probes used for alignment through mistake, the circuit and the parts will be damaged. As the damage is larger than that of ordinary amplifiers and receivers, close attention is needed. It is advised that the turning driver, excluding the top part, should be wrapped with insulation tape or a driver made of plastic or some kind of insulating material should be used.
5. As the dummy load resistor generates heat while alignment, it gets very hot and you may be burnt if you touch it with bare hands. It is better if you can put the dummy load resistor in a place away from being touched, but the wire between the dummy load resistor and the amplifier should not be long. Contrive some method, like putting the dummy load resistor in a well ventilated box. Further, as more than 5 A current might flow in the wire connecting the dummy load resistor and the amplifier, at least larger than AWG #18 thick wire should be used.
6. All the adjustments in the following should be done after the slide switch on the rear panel is set in the "NORMAL" position.

TEST EQUIPMENT

Allow a minimum of 10 minutes warm-up for test equipment.

Maintain rated line voltage.

- Audio Frequency Generator
 - Distortion Meter
 - Oscilloscope
 - AC Voltmeter
 - DC Voltmeter
 - 2-Dummy Load Resistors, 8 ohms, 250 W
- All the semi fixed resistors of the MAIN AMP PCB are set around the center position temporarily. (HVR701 and HVR702.)

IDLING CURRENT ADJUSTMENT

1. Connect the 8 ohms dummy load resistors to the left and right channel speaker terminals.
2. Connect the DC voltmeter across the wiring terminal No. 12 and "TP.L" (left channel) or No. 16 and "TP.R" (right channel). (see Photo 8)
3. Turning on the power switch of the ALPHA 220. Adjust the semi fixed resistor HVR701 (left channel) or HVR702 (right channel) so that the DC voltmeter indicates $18 \text{ mV} \pm 1 \text{ mV}$.
4. Turn off the power switch of the ALPHA 220 and remove the DC voltmeter.

METER CIRCUIT ADJUSTMENT

NOTE: See illustration, Figure 8, for test equipment hook-up.

1. Connect 8 ohms dummy load resistors to the left and right channel speaker terminals.
2. Connect the AC voltmeter, distortion meter and the oscilloscope to the left (right) channel speaker terminals. Connect the generator to left (right) channel input terminal.
3. Turning on the power switch of the ALPHA 220.
4. Set the frequency of the generator to 1 KHz. Adjust the output level of the generator so as to make the output power 98 W. (28 V AC voltmeter reading.)
5. Adjust the semi-fixed resistors of the POWER LEVEL INDICATOR PCB, so that the LED of "120 W" dimly lights up.
6. Turning off the power switch of the ALPHA 220.
7. Remove all test equipment.

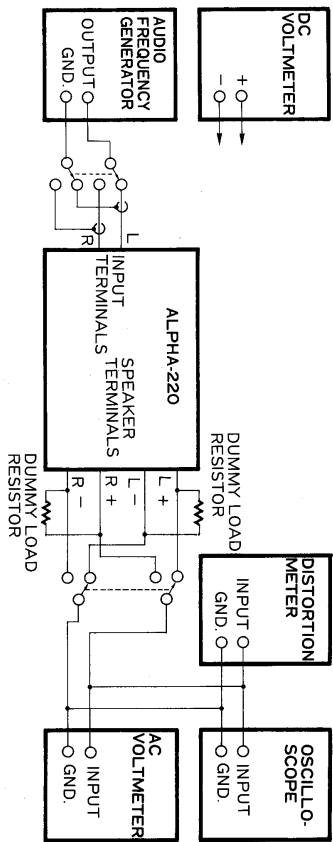


Figure 8 TEST EQUIPMENT HOOK-UP

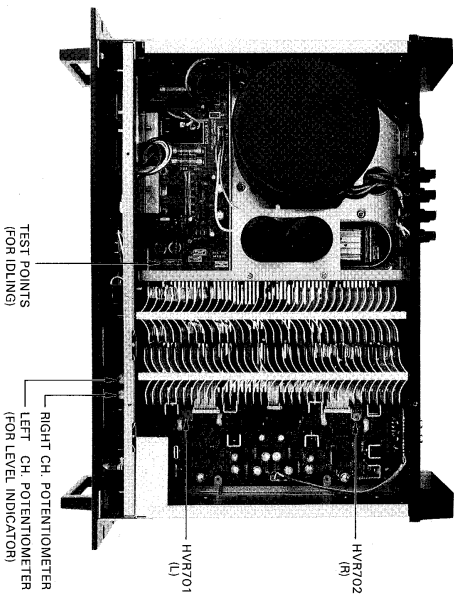


Photo 8 ADJUSTMENT POINTS

POWER TRANSISTORS MOUNTING ASSEMBLY

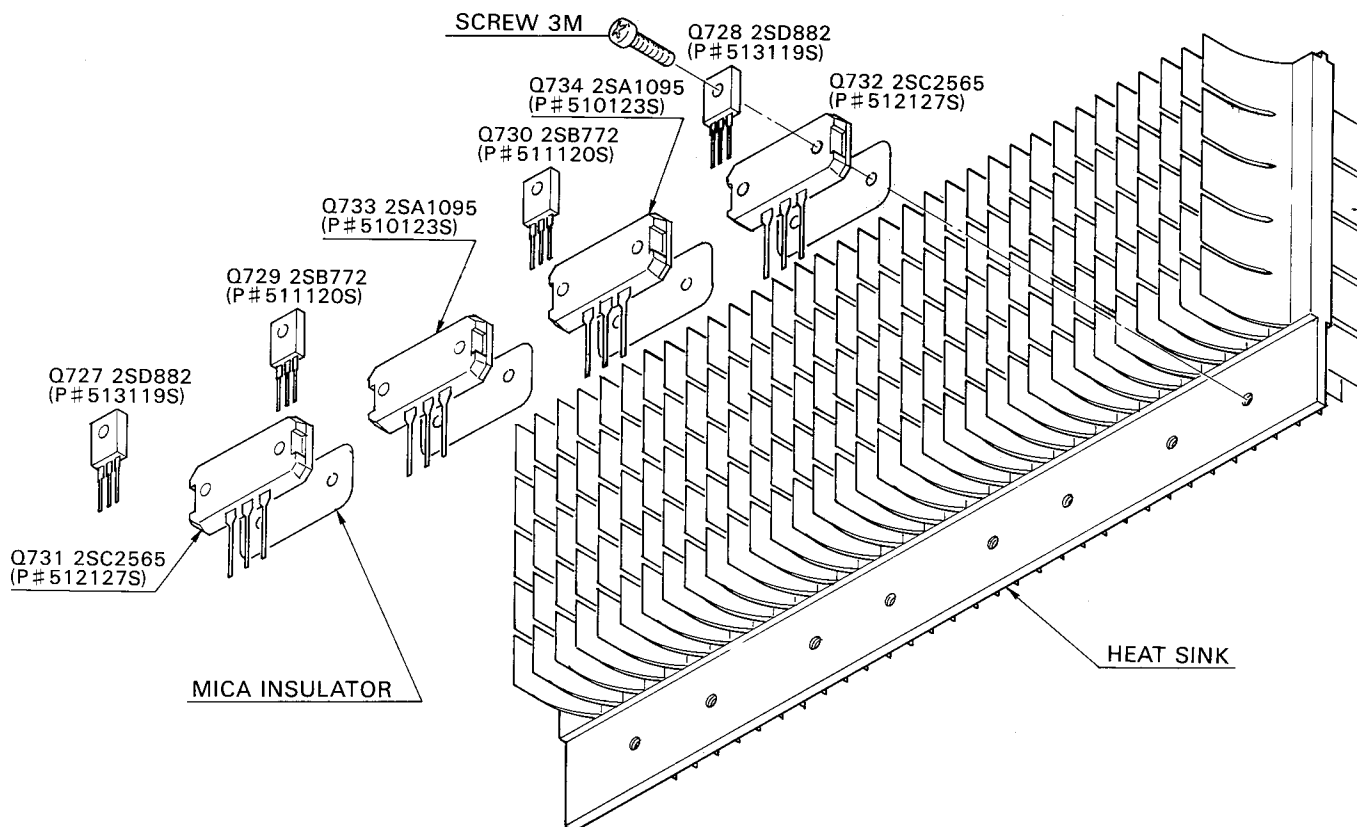


Figure 9

NOTE: For best heat conduction, use thermally conductive silicon grease between the power transistor and the mica insulator and between the insulator and the heat sink.

PRECAUTIONS FOR REPAIR SERVICE

Many of these items are included just as a reminder — they are normal procedures for experienced technicians. Short-cuts can be taken: but, often they cause additional damage to transistors, circuit components or the printed circuit board.

1. Do not bridge electrolytic capacitors with AC power. The resultant surges may damage solid state devices.
2. Do not bias the base of any transistor while voltage is being applied to its collector.
3. Replacements for output and driver transistors, if necessary, must be made from the same hfe group as the original type. Be sure to include this information when ordering replacement transistors.
4. If one output transistor burns out (open or shorts), always remove all output transistors in that channel and check the bias adjustment, the control and other parts in the network with an ohmmeter before inserting a new transistor. All output transistors in one channel will be destroyed if the base biasing circuit is open in the emitter end.

PARTS LIST

1. ★ The KEY NUMBER (#) marked with a (★) on parts list relate to number of three digits with a (○). (Photo 4 ~ 7)
2. + Numerals in file indicate the quantity of parts used in one type.
3. ++ TR : Transistor
 FET : Field effect transistor
 VR : Volume control (Variable resistor)
 RES : Carbon film fixed resistor
 MO-RES : Metal oxide film fixed resistor
 CEM-RES : Cemented wirewound fixed resistor
 FP : Flame proof
 C-CAP : Ceramic capacitor
 E-CAP : Aluminum electrolytic capacitor
 M-CAP : Polyester film capacitor
 S-CAP : Polystyrene film capacitor
 T-CAP : Tantalum electrolytic capacitor
 BP-CAP : Bipolar electrolytic capacitor
 LC-CAP : Low current leakage electrolytic capacitor.

4. Assemblies and parts are subject to change without notice.
5. Parts ordering procedure:
 - A. DO NOT USE THE "KEY" NUMBER AND "SYMBOL" NUMBER. (these are control # for the factory only)
 - B. Include in any order
 - a. Part number.
 - b. Part description.
 - c. Model number.
 (any of the above lacking from an order may delay shipment of that order.)

CAUTION:

The △ mark, the KEY NO. and the SYMBOL NO. circled with rectangle in the schematic diagram and the shaded area in the parts list designate components which have special characteristics important for safety and should be replaced only with types identical to those in the original circuit or specified in the parts list.

KEY NO.	SYMBOL NO.	TYPE ⁺ W E B	DESCRIPTION ⁺⁺	PART NO.
PACKING MATERIALS & ACCESSORIES				
001		1 1 1	Carton box	9825790
002		2 2 2	Pad	9840970
003		1 1 1	Sack, polyethylen cloth	9640740
004		1 1 1	Sack, polyethylen cloth - #13	9640320
005a		1 --	Manual, instructions - English and French	960340E
005b		- 1 1	Manual, instructions - in five different languages	960340K
006		1 --	Manual, safety instructions	9670410
007a		1 --	Card, warranty - U.S.A.	967043A
007b		1 --	Card, warranty - Canada	9670420
008		1 --	List, service stations	9690210
009		1 1 1	Cord, RCA phono pin plug - 2T-1	962014A
CABINET ASSEMBLY				
★101a		1 1 1	Panel, front - SILVER	7885060
★101b		1 1 1	Panel, front - BLACK	7885050
★102a		1 1 1	Panel, power level indicator - SILVER	7870540
★102b		1 1 1	Panel, power level indicator - BLACK	7870490
★103		1 1 1	Window, power level indicator	7802650
★104		1 1 1	Globe, LED - protection indicator	7402540
★105a		2 2 2	Handle - 100G - SILVER	7490180
★105b		2 2 2	Handle - 100B - BLACK	7490190
★106		1 1 1	Guide, button - 1P18 - power switch	7402550
★107		1 1 1	Guide, button - 2P18 - speakers selector	7402560
★108		1 1 1	Globe, LED - input power indicator	7402120
★109a		3 3 3	Button, push - M18GL - power/speakers, SILVER	7852290
★109b		3 3 3	Button, push - M18BK - power/speakers, BLACK	7852300
★110		1 1 1	Cover, top	7821110
111		1 1 1	Plate, bottom	7326430
112		4 4 4	Foot, polyethylen - 22φx10	7401350
CHASSIS ASSEMBLY				
△★201a		1 --	Transformer, power - T-1-397 - AC 120V	1103970
△★201b		- 1 1	Transformer, power - T-1-413 - AC220 or 240V	1104130
★202		1 1 1	Supporter, filter capacitors	7002510
203		1 1 1	Power level indicator assembly	4582770
★204		1 1 1	Inside panel, power level indicator	7802660
★205		1 1 1	Light guide, level indicator	7401580
206		1 1 1	Lamp - 8V 0.3A	5808210
BACK PLATE ASSEMBLY				
★301a		1 --	Plate, back - (W)	7326390
★301b		- 1 1	Plate, back - (E)	7326400
★302		2 2 2	Block, terminal guard	7401860
★303		2 2 2	Terminal, speakers - screw type 4P	4450480

KEY NO.	SYMBOL NO.	TYPE ⁺ W E B	DESCRIPTION ⁺⁺	PART NO.
△★304a		1 --	Cord, AC line - SPT-1	606010A
△★304b		- 1 --	Cord, AC line - CEE-2T	600508A
△★304c		- - 1	Cord, AC line - BS	600515A
△★305a		1 --	Bush, power cord - SR-3P-4	7400620
△★305b		- 1 1	Bush, power cord - SR-4N-4	7400690
MAIN AMP PC BOARD ASSEMBLY				
(POWER OUTPUT SECTION)				
Q727,728		2 2 2	TR 2SD882 (P or Q)	513119S
Q729,730		2 2 2	TR 2SB772 (P or Q)	511120S
Q731,732,				
Q735,736		4 4 4	TR 2SC2565 (O or R)	512127S
Q733,734,				
Q737,738		4 4 4	TR 2SA1095 (O or R)	510123S
C741,742		2 2 2	M-CAP 0.047uf 10% 400V	273473K
C743				
~ C746		4 4 4	E-CAP 1uf 100V	211810Q
R781				
~ R788		8 8 8	CEM-RES 0.1ohm 2Wx2	382109P
R789,790		2 2 2	FP-MO-RES 10ohm 2W	362100L
(DRIVER PCB SECTION)				
IC701		1 1 1	IC AN6552	518096S
Q701,702		2 2 2	FET 2SK 150A (GR)	516038S
Q703				
~ Q706		4 4 4	TR 2SC1845 (E or F)	512115S
Q707				
~ Q710		4 4 4	TR 2SA1144 (O or Y)	510120S
Q711,712		2 2 2	TR 2SC1941 (L or K)	512112S
Q713,714		2 2 2	TR 2SC2704 (O or Y)	512122S
Q715,716		2 2 2	TR 2SA992 (E or F)	510110S
Q717,718		2 2 2	TR 2SC1845 (E or F)	512115S
Q719,720		2 2 2	TR 2SC1815 (Y or GR)	512107S
Q721,722		2 2 2	TR 2SA1015 (Y or GR)	510102S
Q723,724		2 2 2	TR 2SC2275 (P or Q)	512120S
Q725,726		2 2 2	TR 2SA985 (P or Q)	510118S
D701				
~ D704		4 4 4	Diode 2-0A90	500013G
D705				
~ D708		4 4 4	Diode 1S2076	501019S
D709,710		2 2 2	Diode GP10-4002	560066S
D802		1 1 1	Diode W02	560061S
ZD701				
~ ZD704		4 4 4	Zener diode RD22EB4	502059S
ZD705,706		2 2 2	Zener diode RD13EB3	502063S
TH701				
~ TH704		4 4 4	Thermistor D2FHL-103S	5400180

SEMICONDUCTOR DATA

TRANSISTORS

† NOTES Ge: Germanium
Si: Silicon

A: Alloy
B: Base
D: Diffused
Dd: Double-diffused

Df: Drift-field
E: Epitaxial
G: Grown
J: Junction

M: Mesa
P: Planer
Pc: Point-contact
Td: Triple-diffused

DEVICE TYPE	APPLICATIONS	STRUCTURE†	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)						ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)														MANUFACTURER
			Collector-to-Base Voltage VCB0 (V)	Emitter-to-Base Voltage VEB0 (V)	Collector Current IC (mA)	Collector Dissipation Pc (mW)	Junction Temperature TJ (°C)	Collector Cutoff Current ICBO (μA)	VCB (V)	hFE	VCE (V)	IC (mA)	VCESat (V)	IC (mA)	IB (mA)	fT (MHz)	VCE (V)	IE (mA)	Output Capacitance Cob (pF)	Others			
2SA985 (P, Q)	AF, Power amp.	PNP Si-E	-120	-5	-1.5A	25W (Tc=25°C)	150	-1 max.	-120	100 ~ 320	-5	-300	-2 max.	-1A	-100	180	-5	-200*	29	Complementary to 2SC2275	NEC		
2SA992 (E, F)	AF, Low noise	PNP Si-E	-120	-5	-50	500	125	-0.05 max.	-120	300 ~ 800	-6	-0.1	-0.3 max.	-10	-1	100	-6	1	3 max.	Complementary to 2SC1845	NEC		
2SA1015 (Y, GR)	AF, General	PNP Si-E	-50	-5	-150	400	125	-0.1 max.	-50	120 ~ 400	-6	-2	-0.3 max.	-100	-10	80 min.	-10	-1*	7 max.	Complementary to 2SC1815	TOSHIBA		
2SA1095 (O, R)	AF, Power amp.	PNP Si-E	-160	-5	-15A	150W (Tc=25°C)	150	-50 max.	-160	55 ~ 160	-5	-1A	-2 max.	-5A	-500	60	-10	-1A*	350	Complementary to 2SC2565	TOSHIBA		
2SA1144 (O, Y)	AF, Driver	PNP Si-E	-150	-5	-50	10W (Tc=25°C)	150	-0.1 max.	-150	80 ~ 240	-5	-10	1 max.	-10	-1	120	-5	-10*	2.5	Complementary to 2SC2704	TOSHIBA		
2SB772 (P, Q)	AF, Power amp.	PNP Si-E	-40	-5	-3A	1W	150	-1 max.	-30	100 ~ 320	-2	-20	-0.5 max.	-2A	-200	80	-5	100	55	Complementary to 2SD882	NEC		
2SC1815 (Y, GR)	AF, General	NPN Si-E	60	5	150	400	125	0.1 max.	60	120 ~ 400	6	2	0.25 max.	100	10	80 min.	10	1*	3 max.	Complementary to 2SA1015	TOSHIBA		
2SC1845 (E, F)	AF, Low noise	NPN Si-E	120	5	50	500	125	0.05 max.	120	300 ~ 800	6	0.1	0.3 max.	10	1	110	6	-1	2.5 max.	Complementary to 2SA992	NEC		
2SC1941 (L, K)	AF, Driver	NPN Si-E	160	5	50	800	150	0.1 max.	160	135 ~ 400	10	1	0.6 max.	20	2	120	10	-10	3 max.		NEC		
2SC2229 (O, Y)	AF, Driver	NPN Si-Td	200	5	50	800	150	0.1 max.	200	70 ~ 240	5	10	0.5 max.	10	1	120	30	10*	5 max.		TOSHIBA		
2SC2235 (O, Y)	AF, Driver	NPN Si-E	120	5	800	900	150	1 max.	120	80 ~ 240	5	100	1 max.	500	50	120	5	100*	30 max.		TOSHIBA		
2SC2240 (GR, BL)	AF, Low Noise	NPN Si-E	120	5	100	300	125	0.1 max.	120	200 ~ 700	6	2	0.3 max.	10	1	100	6	1*	3		TOSHIBA		
2SC2275 (P, Q)	AF, Power amp.	NPN Si-E	120	5	1.5A	25W (Tc=25°C)	150	1 max.	120	100 ~ 320	5	300	2 max.	1A	100	200	5	200*	19	Complementary to 2SA985	NEC		
2SC2565 (O, R)	AF, Power amp.	NPN Si-E	160	5	15A	150W (Tc=25°C)	150	50 max.	160	55 ~ 160	5	1A	2 max.	5A	500	80	10	1A*	200	Complementary to 2SA1095	TOSHIBA		
2SC2704 (O, Y)	AF, Driver	NPN Si-E	150	5	50	10W (Tc=25°C)	150	0.1 max.	150	80 ~ 240	5	10	1 max.	10	1	200	5	10*	1.8	Complementary to 2SA1144	TOSHIBA		
2SD882 (P, Q)	AF, Power amp.	NPN Si-E	40	5	3A	1W	150	1 max.	30	100 ~ 320	2	20	0.5 max.	2A	200	90	5	-100	45	Complementary to 2SB772	NEC		

FIELD EFFECT TRANSISTOR

DEVICE TYPE	APPLICATIONS	STRUCTURE†	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)								ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)												MANUFACTURER		
			Gate-to-Drain Voltage VGDO (V)	Gate-to-Source Voltage VGSO (V)	Gate Current IG (mA)	Drain Current ID (mA)	Total Dissipation Pd (mW)	Channel Temperature Tch (°C)	Gate Leak Current (Test Conditions)	IGSS (nA)	Gate to Drain Breakdown Voltage (Test Conditions)	VBR1 (V)	Drain Current IDSS (mA)	Gate to Source Cutoff Voltage (Test Conditions)	VGS (off) (V)	Forward Transfer (Test Conditions)	IVel (mV)	Feed Back Capacitance (Test Conditions)	CSS (pF)	Power Gain (Common Source) (Test Conditions)	GPS (dB)	Noise Figure (Test Conditions)		NF (dB)	
2SK150 A (GR)	AF, Low noise Differential amp.	Si N-channel junction (Dual)	-50	-50	10		200/unit	125	VGS = -30V VDS = 0	-1 max.		VDS = 10V VGS = 0	2.6 ~ 6.5			12	VDS = 10V VGS = 0 f = 1 kHz ID = 1 mA f = 1 kHz	3					VDS = 10V ID = 1 mA f = 1 kHz	2 max.	TOSHIBA

DIODES, LED'S

DEVICE TYPE	APPLICATIONS	STRUCTURE†	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)								ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)										MANUFACTURER			
			Reverse Surge Voltage VRsurge (V)	Peak Reverse Voltage VRM (V)	Reverse Voltage VR (V)	Peak Forward Voltage VFM (V)	Peak Forward Current IFM (mA)	Average Rectified Current IO (mA)	Forward Surge Current IF surge (A)	Junction Temperature TJ (°C)	Total Power Dissipation Pd (mW)	Forward Current Imin (mA)	Test Condition VF (V)	Forward Voltage Vmax (V)	Test Condition IF (mA)	Reverse Current Irm (μA)	Test Condition VR (V)	Others						
2-0A90	Detector	Ge-Pc			15		150		0.4	75		4	1											MATSUSHITA
1S2076	Medium speed Switching	Si-EP		35	30		450	150	1	175	250		0.8	10	1	30								HITACHI
1S2076A	Medium speed Switching	Si-EP		70	60		450	150	1	175	250		0.8	10	1	30								HITACHI
GP10-4002	Rectifier	Si-DJ		100	70			1A	30	175			1.1	1A	5									GENERAL INSTRUMENT
W02	Rectifier	Si-DJ (Bridge)			200	200		1.5A	50	125			1.0	1A	10							Rth = 50°C/W		GENERAL INSTRUMENT
S10VB20	Rectifier	Si-DJ (Bridge)			200			10A	200	150			1.05		10									SHINDENGEN
BR5504S	Lamp (red)	GaAlAs			4		300		IF = 50	85	100		2.0	20	100	4						IV = 80 mcd (IF = 20 mA)		STANLEY
PR5527S	Lamp (red)	GaP			4		100		IF = 30	85	75		2.0	10	100	4						IV = 1.2 mcd (IF = 10 mA)		STANLEY

ZENER DIODES

DEVICE TYPE	APPLICATIONS	STRUCTURE†	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)			ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)												MANUFACTURER						
			Total Power Dissipation Pd (mW)	Zener Current IZ (A)	Junction Temperature TJ (°C)	Zener Voltage VZ			Differential Resistance rZ			Temperature Coefficient γZ			Reverse Current IZ				Others					
			MIN (V)	TYP (V)	MAX (V)	IZ (mA)	TYP (Ω)	MAX (Ω)	IZ (mA)	MAX (mV/°C)	MAX (%/°C)	IZ (mA)	MAX (μA)	VR (V)										
RD13EB3	Regulator	Si-J	400		175	12.99		13.66	10		25	10												NEC
RD22EB4	Regulator	Si-J	400		175	21.52		22.63	5		60	5												NEC

INTEGRATED CIRCUITS AN6552

- **Manufacturer:** MATSUSHITA
- **Applications:** Dual Operational Amplifier

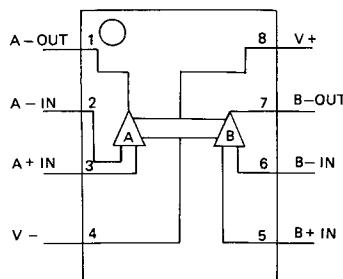
ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±18 V	Input Voltage	±15 V
Internal Power Dissipation	500 mW	Storage Temperature Range	-40°C to +125°C
Differential Input Voltage	±30 V	Operating Temperature Range	-20°C to +75°C

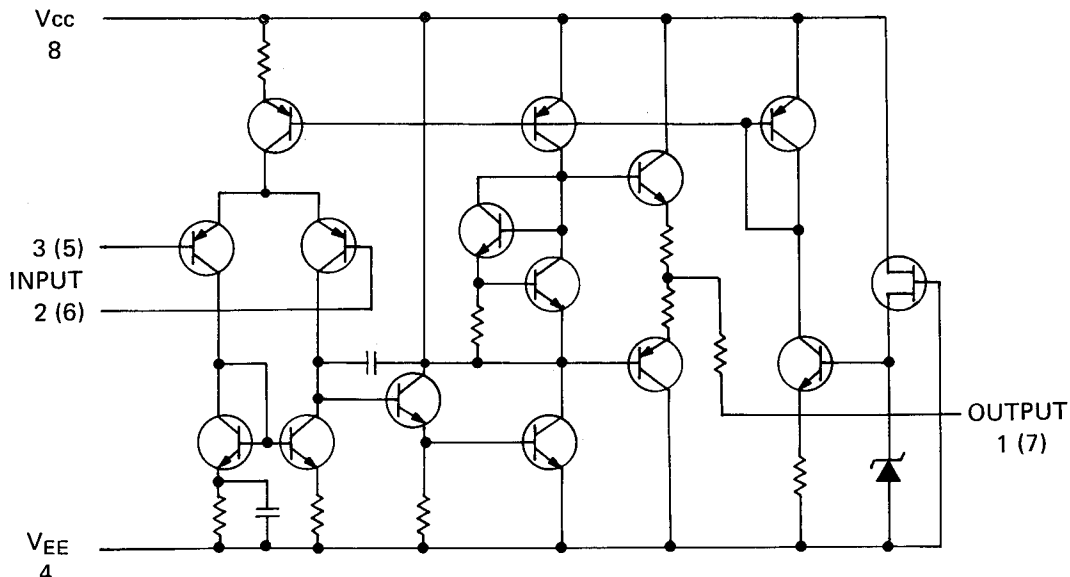
ELECTRICAL CHARACTERISTICS ($V_{CC} = \pm 15V$, $T_A = +25^\circ C$ unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Input Offset Voltage	$R_S \leq 10\text{ k}\Omega$		0.5	6.0	mV
Input Offset Current			5	200	nA
Input Bias Current				500	nA
Large-Signal Voltage Gain	$R_L \geq 2\text{ k}\Omega$ $V_{out} = \pm 10V$	86	100		dB
Output Voltage Swing	$R_L \geq 2\text{ k}\Omega$	±10	±13		V
Common Mode Rejection Ratio	$R_S \leq 10\text{ k}\Omega$	70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10\text{ k}\Omega$		30	150	$\mu V/V$
Slew Rate	$R_L \geq 2\text{ k}\Omega$		1		V/ μS

TERMINAL GUIDE (TOP VIEW)



SCHEMATIC DIAGRAM (1/2 CIRCUIT)



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Important Information for your Parts and Service Department

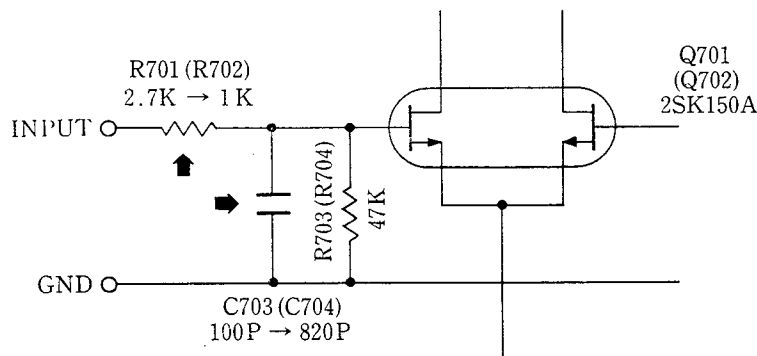
MODEL: ALPHA 220

ASSEMBLY: DRIVER PCB

For the purpose of protecting the transistors in the power stage, replace capacitors and resistors on the DRIVER P.C. BOARD.

1. Capacitors C703 and C704 (100 pf) are replaced with new ones (820 pf).
2. Resistors R701 and R702 (2.7 kohms) are replaced with new ones (1 kohms).

These modifications are already done for the units bearing Serial No. C6534701 and up.



PARTS LIST

DELETE		
SYMBOL No.	DESCRIPTION	PART No.
C703, 704	Ceramic capacitor 100pf 10% 50V	232101K
R701, 702	Carbon film resistor 2.7 kohms 5% 1/4W	328272J

ADD		
SYMBOL No.	DESCRIPTION	PART No.
C703, 704	Ceramic capacitor 820pf 10% 50V	232821K
R701, 702	Carbon film resistor 1 kohms 5% 1/4W	328102J

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